Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameters)
PART NUMBER: TPCA8004-H
MANUFACTURER: TOSHIBA
Body Diode (Model Parameters) / ESD Protection Diode

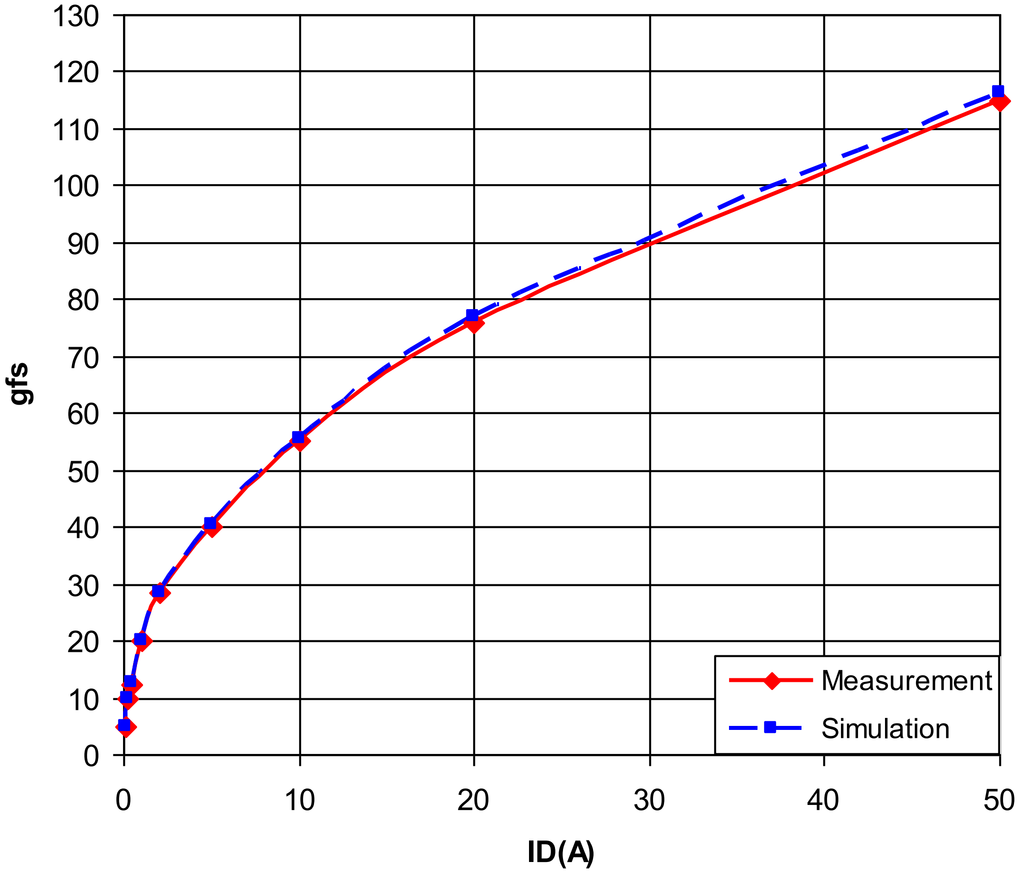
Bee Technologies Inc.

MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

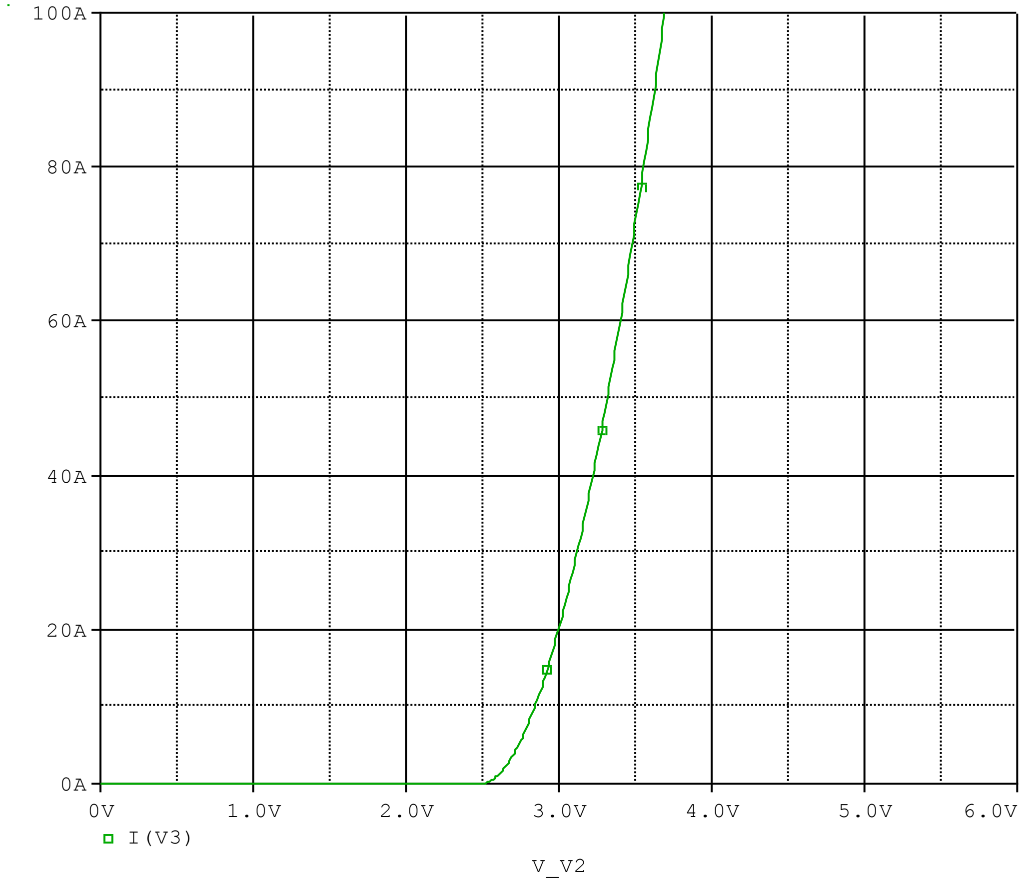


Comparison table

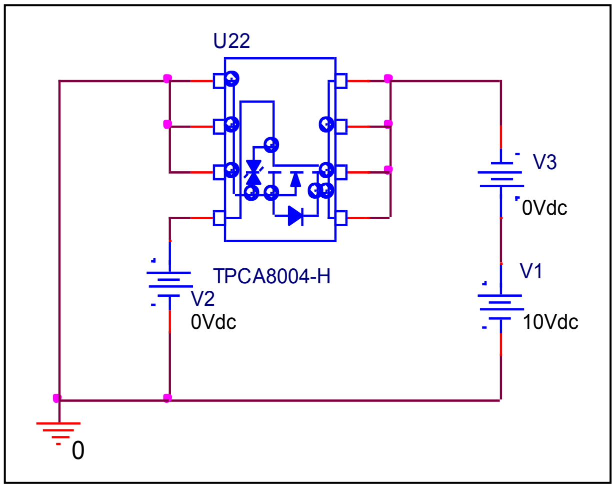
Id(A)	gfs		Error(%)
	Measurement	Simulation	
0.1	5.000	5.000	0.000
0.2	10.000	10.000	0.000
0.5	12.400	12.500	0.806
1	20.000	20.000	0.000
2	28.500	28.571	0.249
5	40.000	40.461	1.153
10	55.000	55.555	1.009
20	76.000	76.923	1.214

Vgs-Id Characteristic

Circuit Simulation result

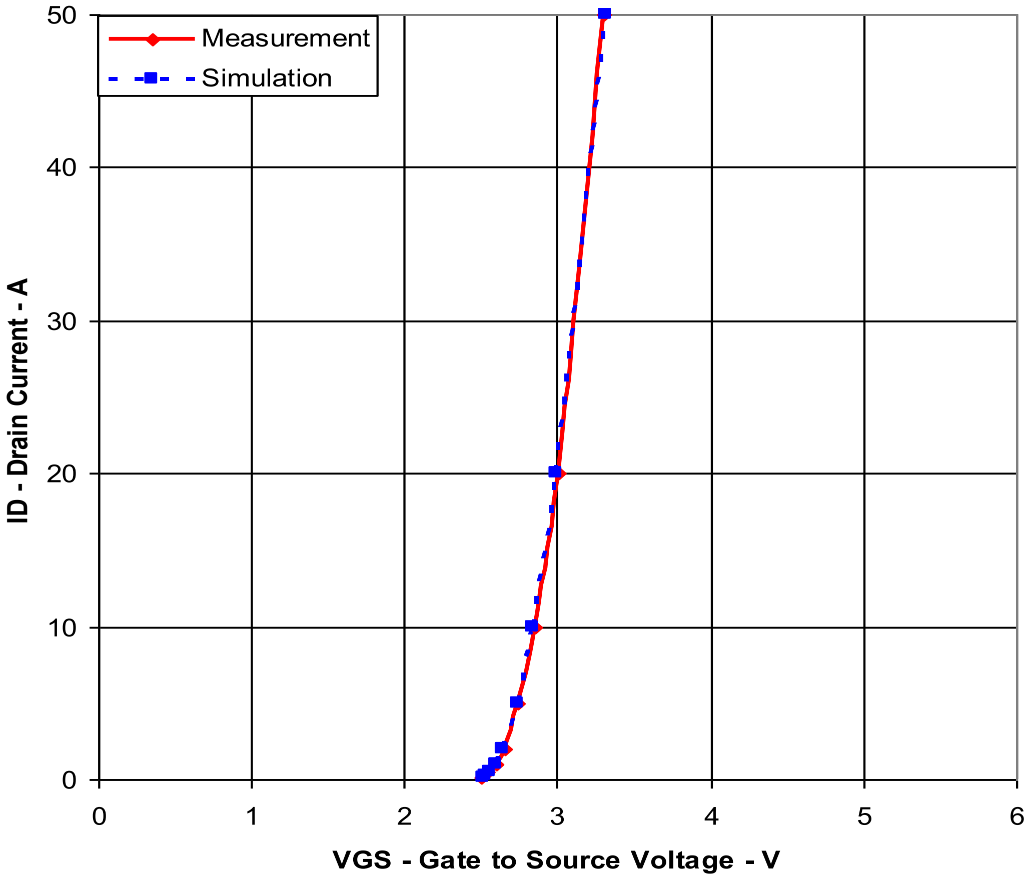


Evaluation circuit



Comparison Graph

Circuit Simulation Result

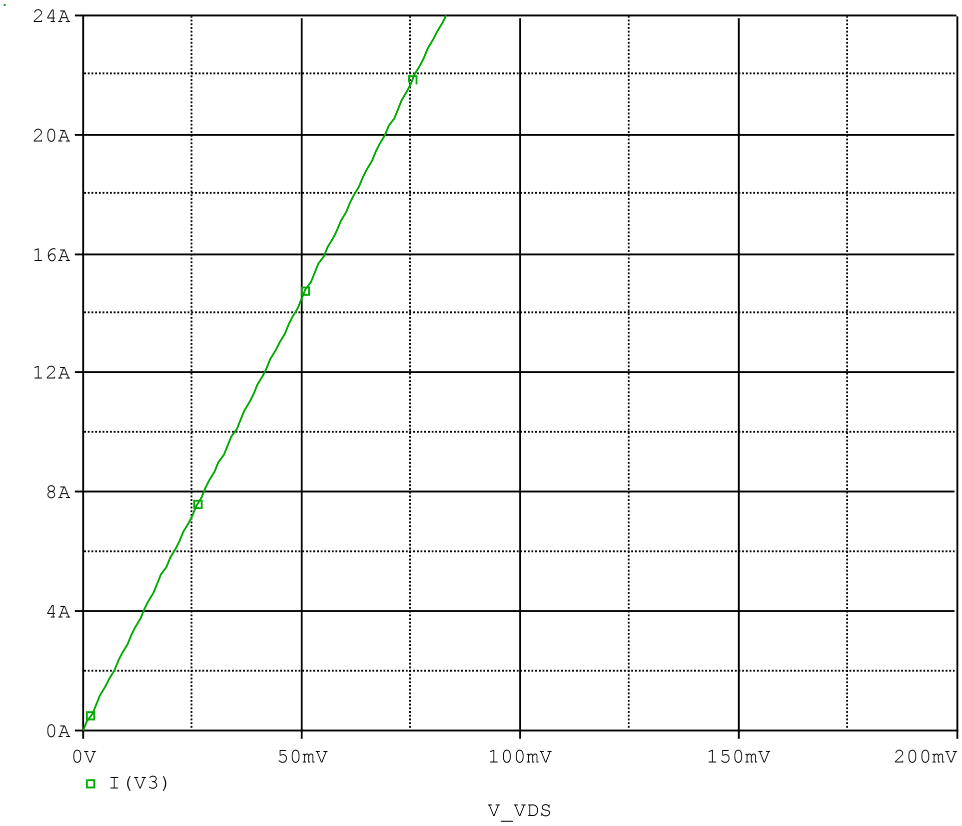


Simulation Result

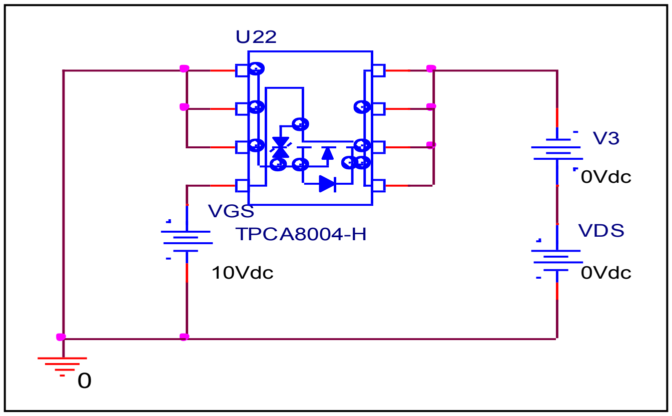
I_D(A)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
0.1	2.500	2.518	0.720
0.2	2.520	2.533	0.516
0.5	2.550	2.562	0.471
1	2.600	2.595	-0.192
2	2.650	2.642	-0.302
5	2.740	2.735	-0.182
10	2.850	2.843	-0.246
20	3.000	2.998	-0.067
50	3.300	3.317	0.515

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

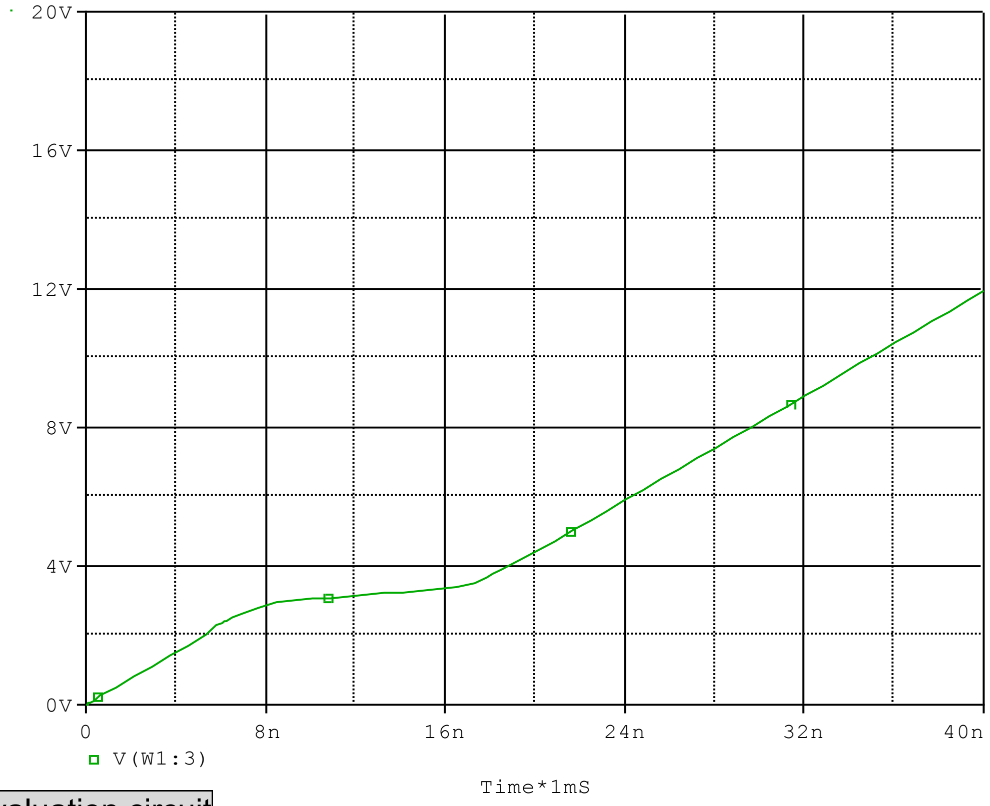


Simulation Result

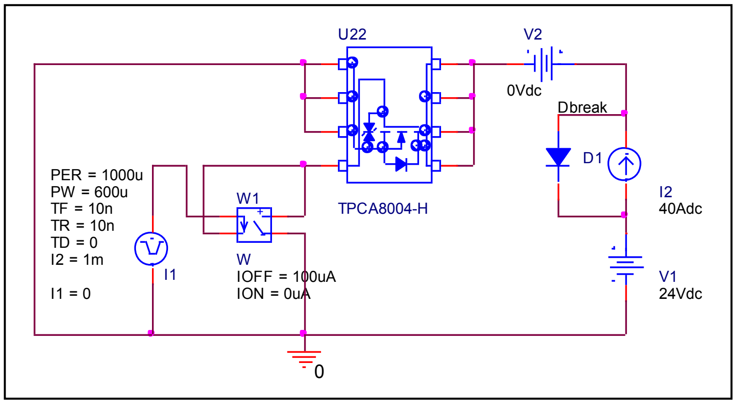
I_D=20A, V_{GS}=10V	Measurement		Simulation		Error (%)
R_{DS} (on)	0.0035	Ω	0.00349	Ω	-0.286

Gate Charge Characteristic

Circuit Simulation result



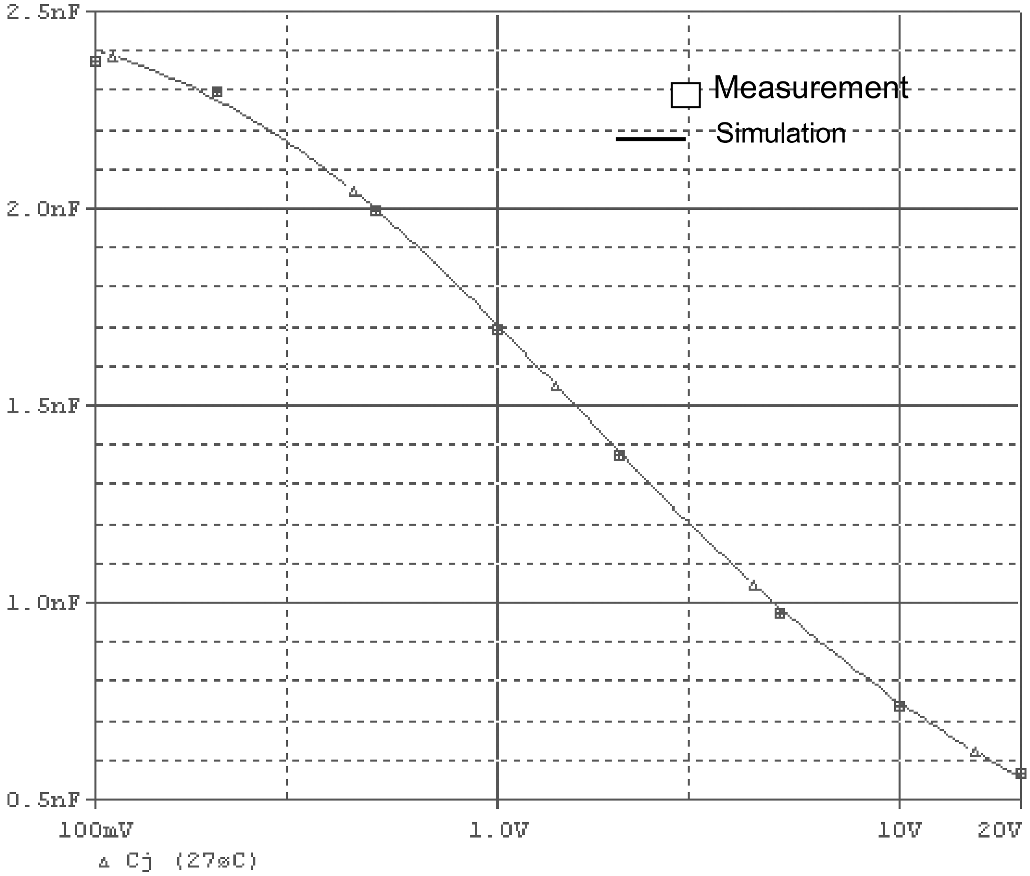
Evaluation circuit



Simulation Result

V_{DD}=24V,I_D=40A ,V_{GS}=10V	Measurement	Simulation	Error (%)
Qgs(nC)	8.200	8.214	0.171
Qgd(nC)	8.700	8.750	0.575
Qg	37.00	34.911	-5.646

Capacitance Characteristic

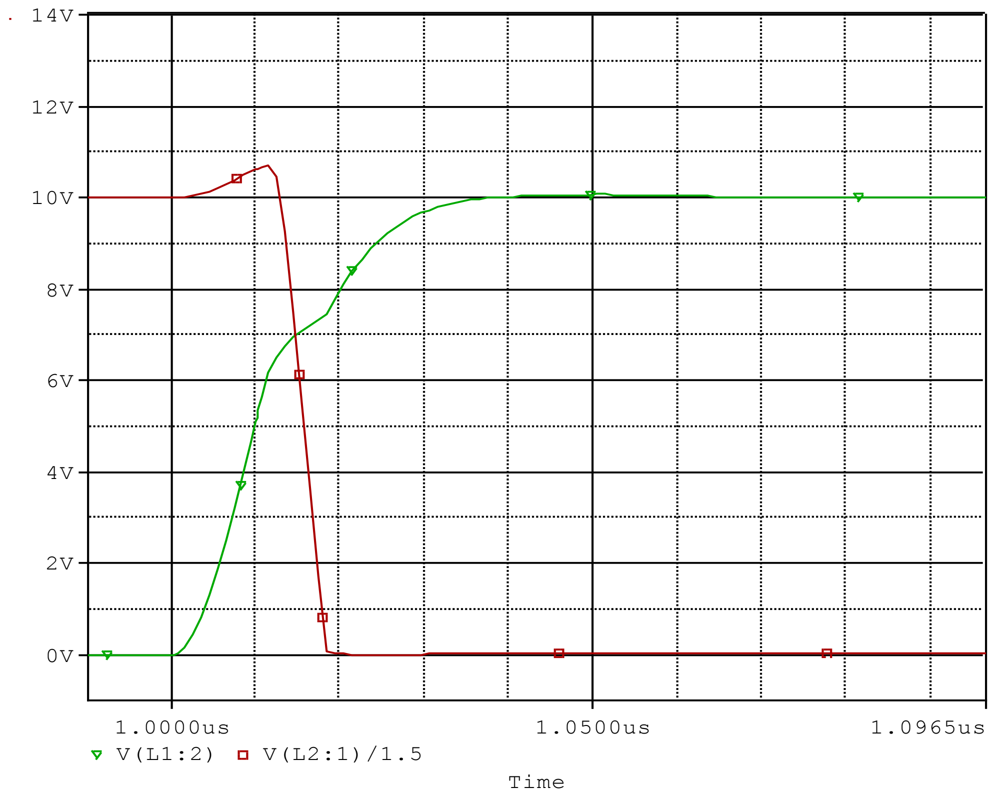


Simulation Result

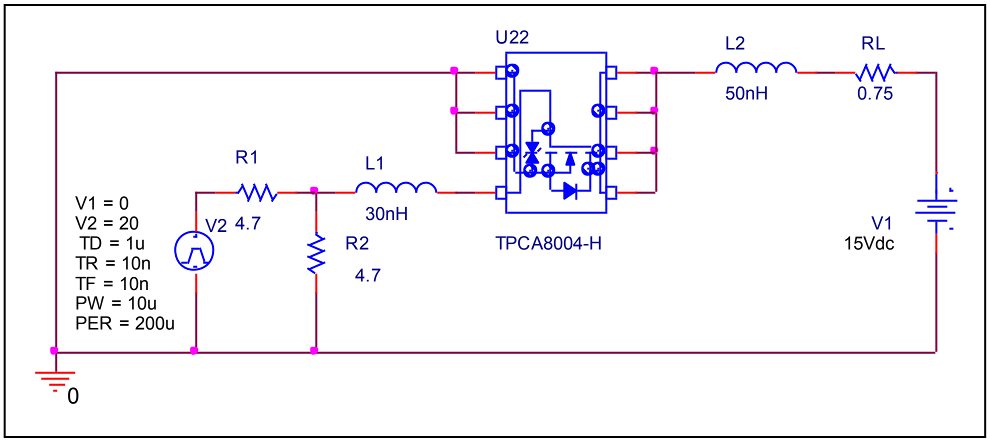
V_{DS}(V)	Cbd(pF)		Error(%)
	Measurement	**Simulation**	
0.1	**2380**	**2400**	**0.840**
0.2	**2300**	**2290**	**-0.435**
0.5	**2000**	**2005**	**0.250**
1	**1700**	**1703**	**0.176**
2	**1380**	**1385**	**0.362**
5	**980**	**984**	**0.408**
10	**740**	**742**	**0.270**
20	**570**	**569**	**-0.175**

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

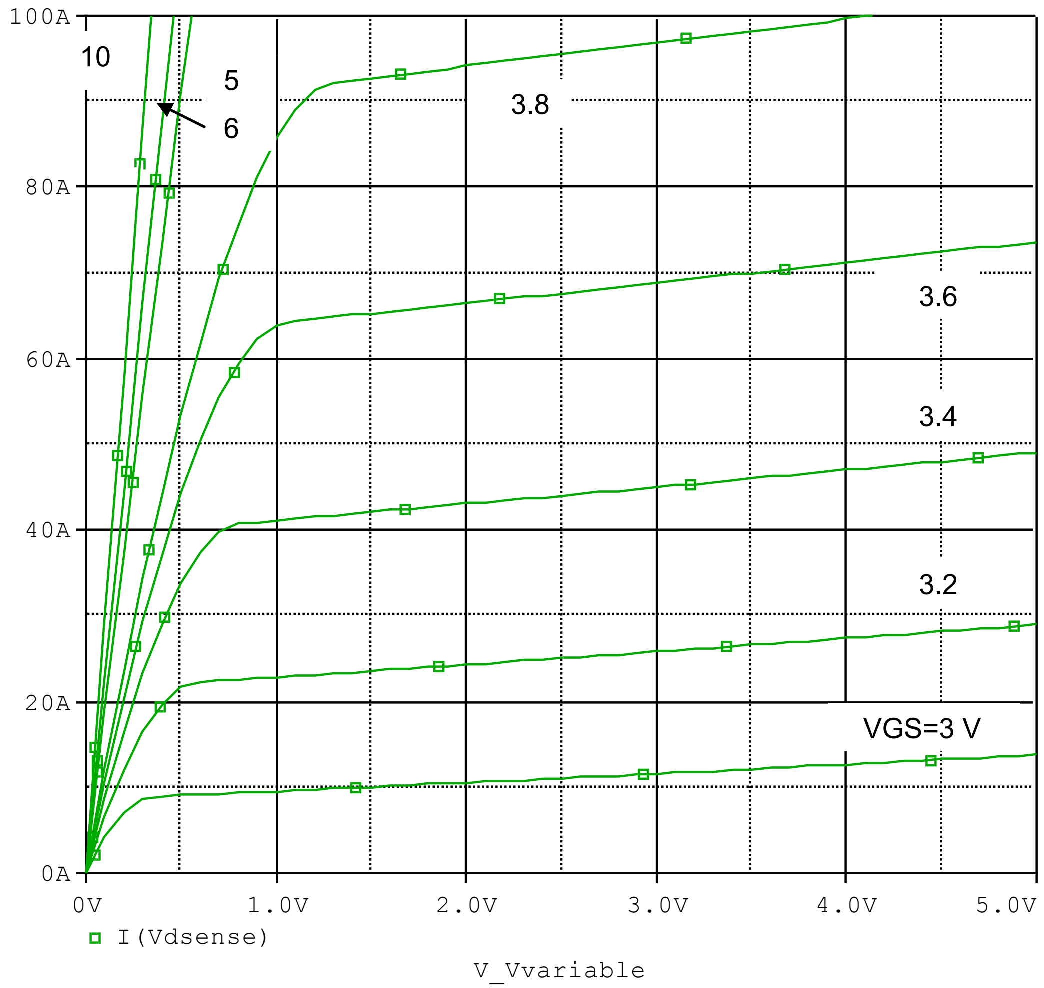


Simulation Result

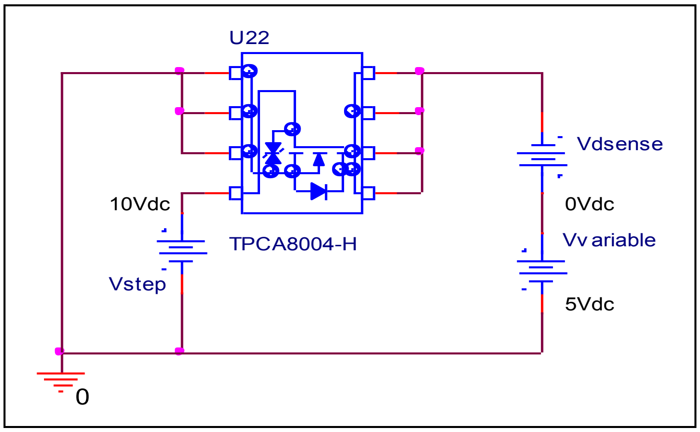
I_D=20 A, V_{DD}=15V V_{GS}=0/10V	Measurement	Simulation	Error(%)
Ton(ns)	14.000	14.107	0.764

Output Characteristic

Circuit Simulation result

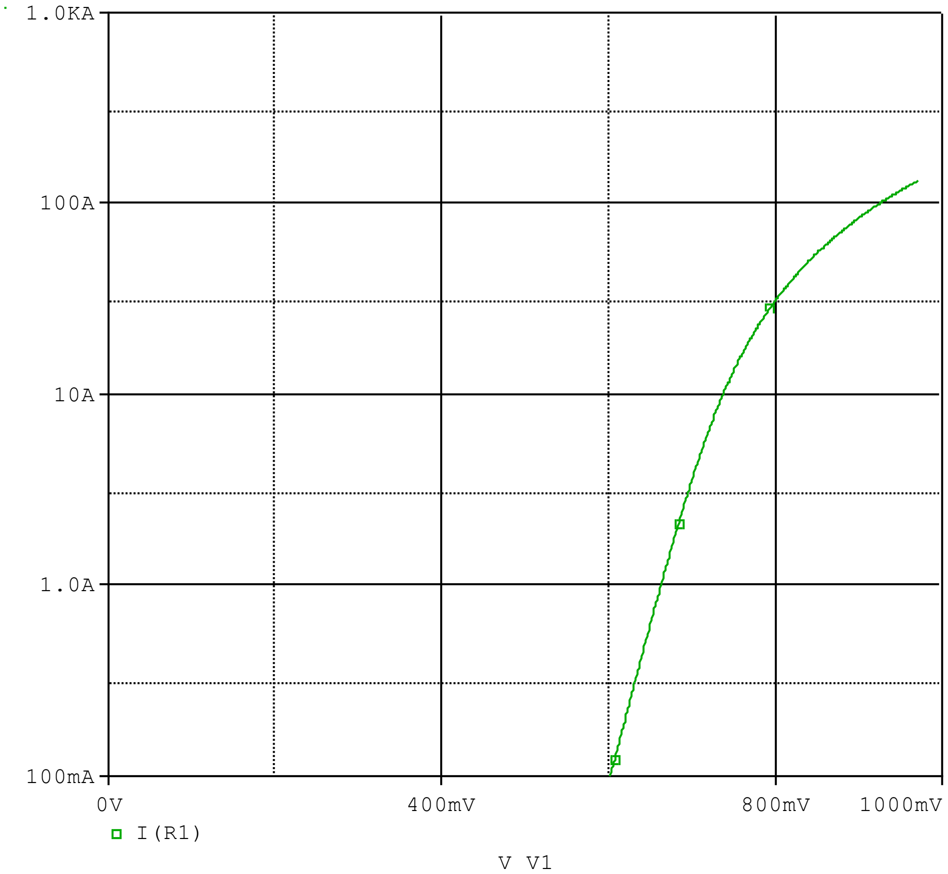


Evaluation circuit

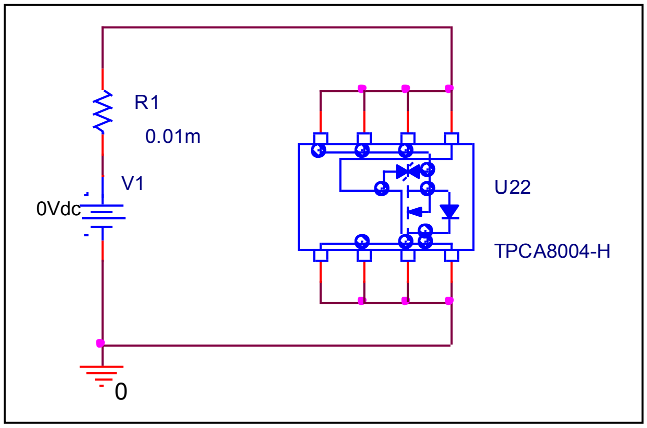


BODY DIODE
Forward Current Characteristic

Circuit Simulation Result

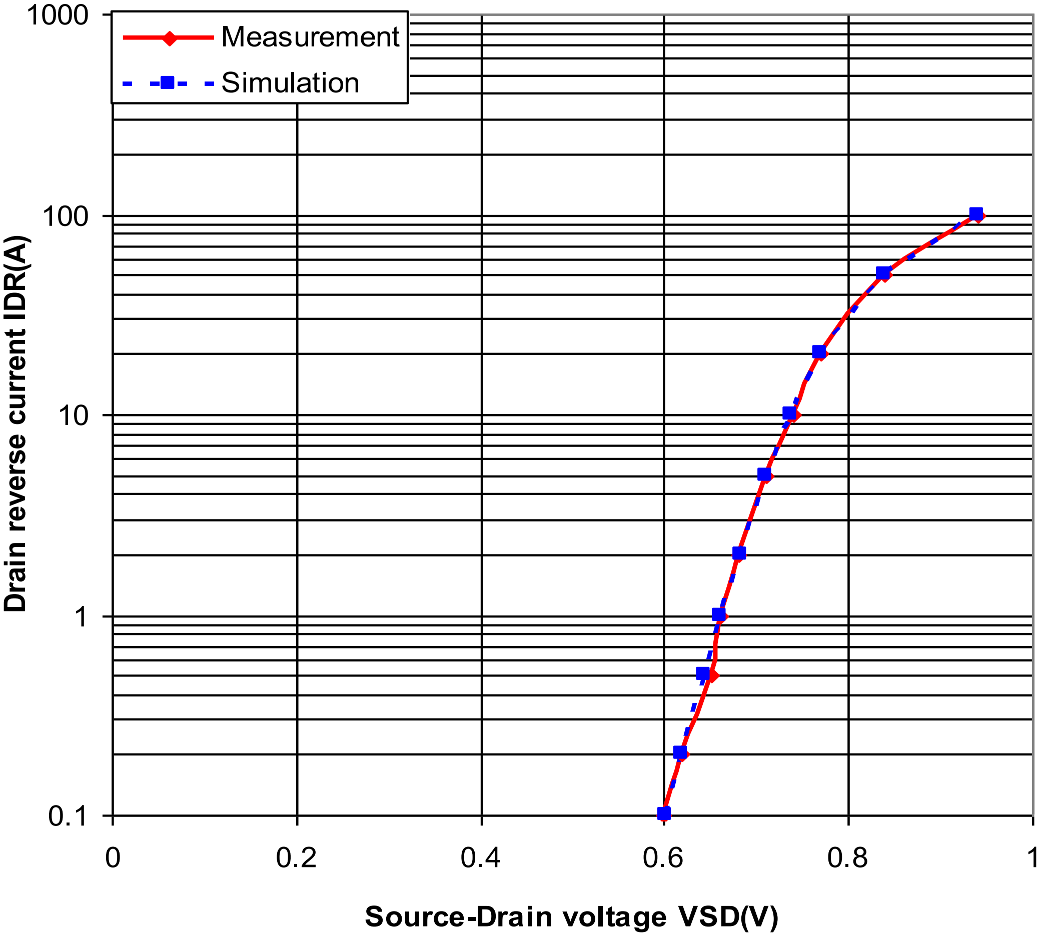


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

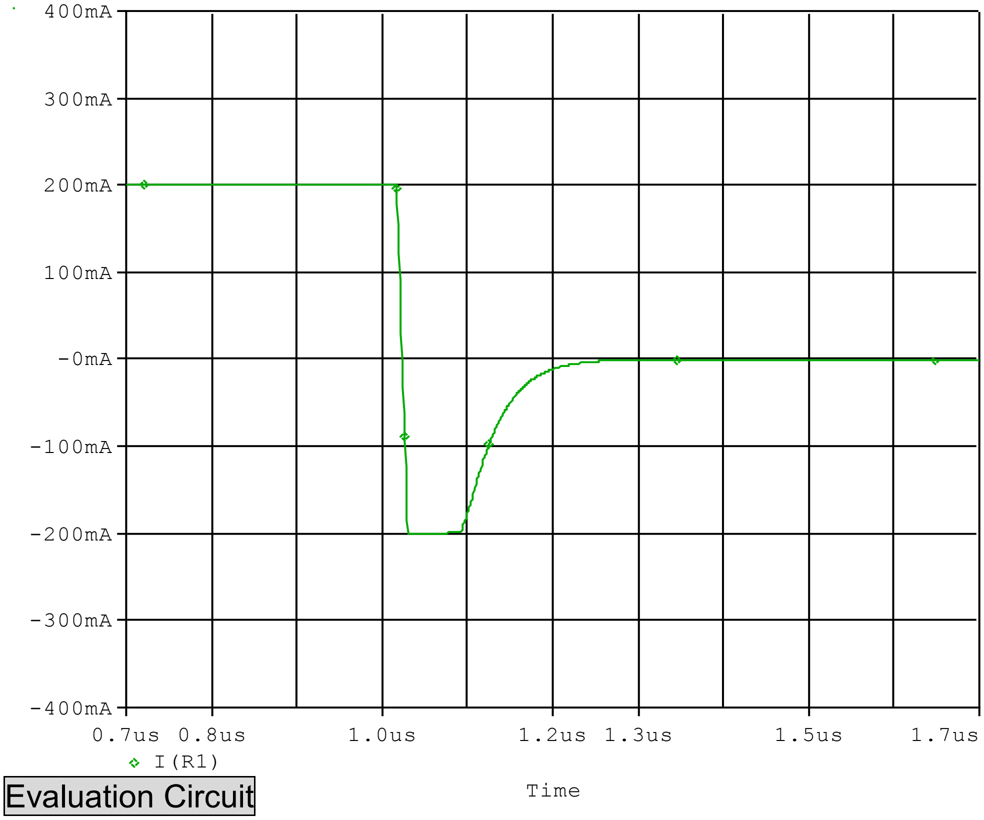


Simulation Result

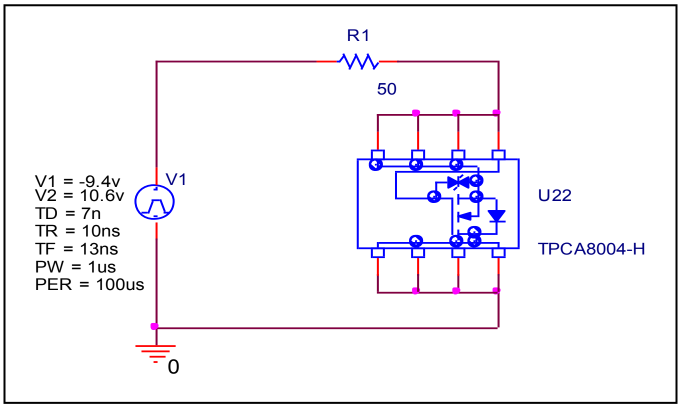
IDR(A)	VSD(V)		%Error
	Measuremen	Simulation	
0.1	0.600	0.601	0.167
0.2	0.620	0.620	0.000
0.5	0.650	0.644	-0.923
1	0.660	0.662	0.303
2	0.680	0.682	0.294
5	0.710	0.711	0.141
10	0.740	0.737	-0.405
20	0.770	0.771	0.130
50	0.840	0.840	0.000

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

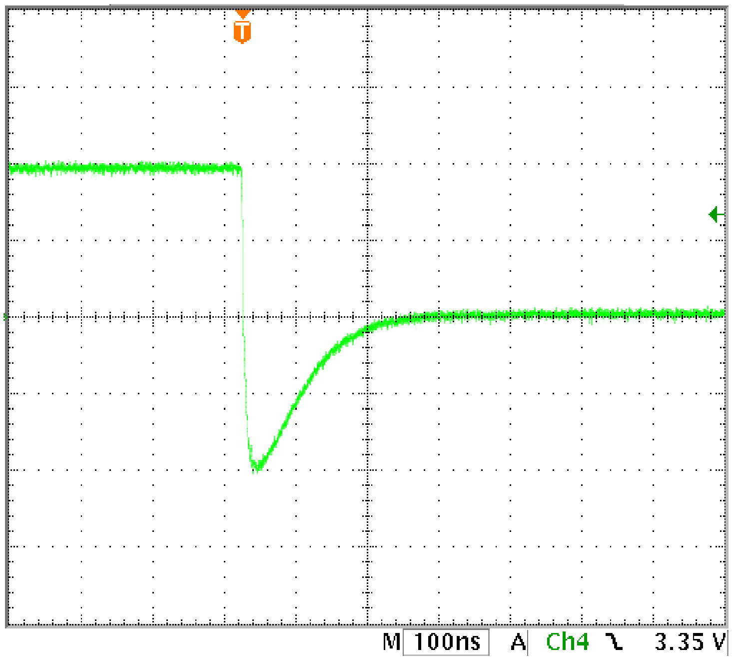


Compare Measurement vs. Simulation

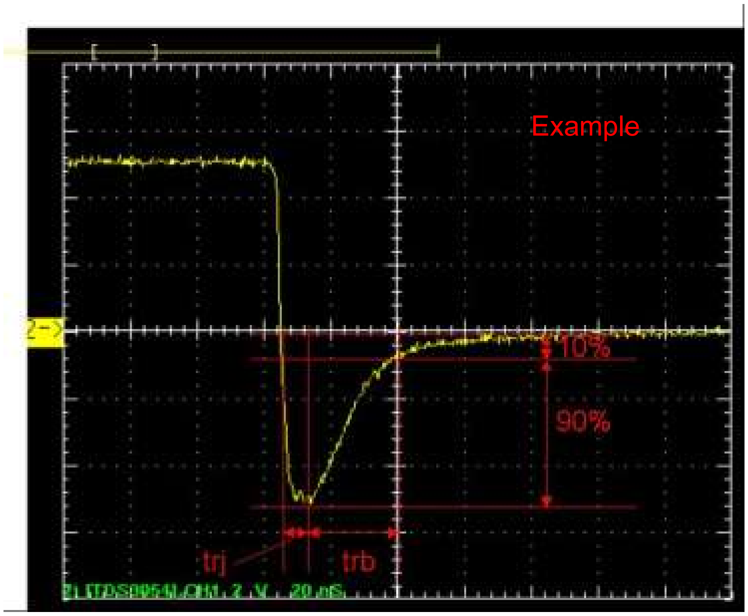
Trr(ns)	Measurement	Simulation	Error (%)
Trj+Trb(ns)	158.500	158.393	-0.068

Reverse Recovery Characteristic

Reference



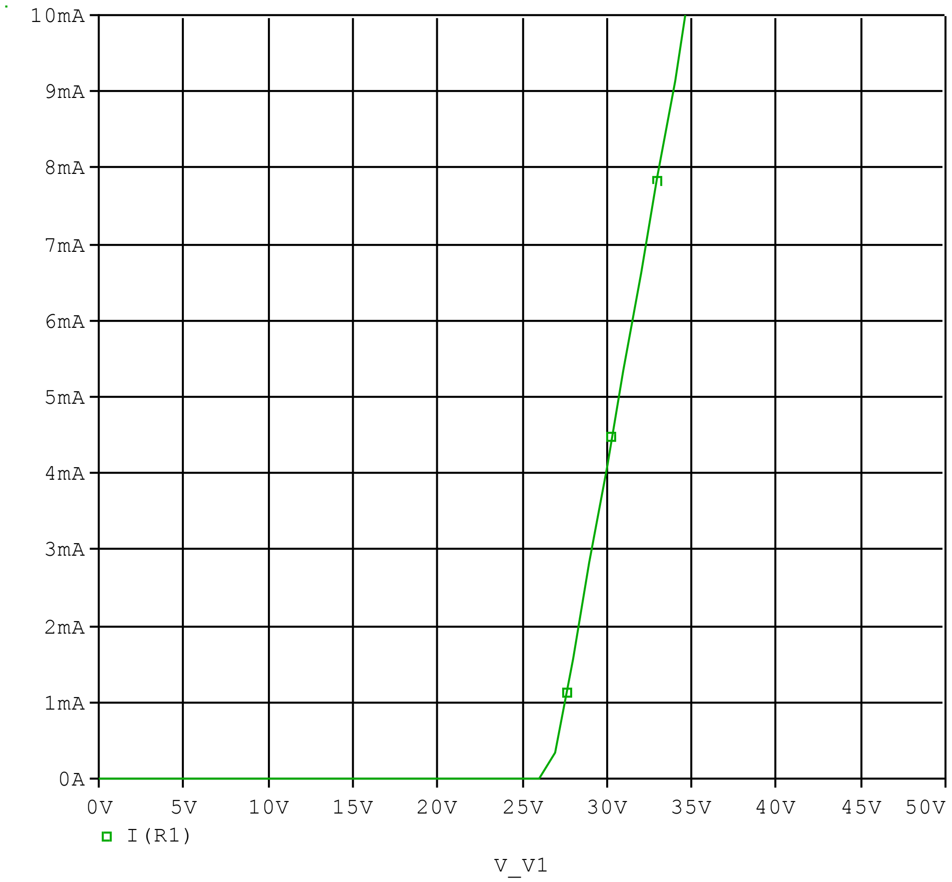
Trj=18.5(ns)
Trb=140ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



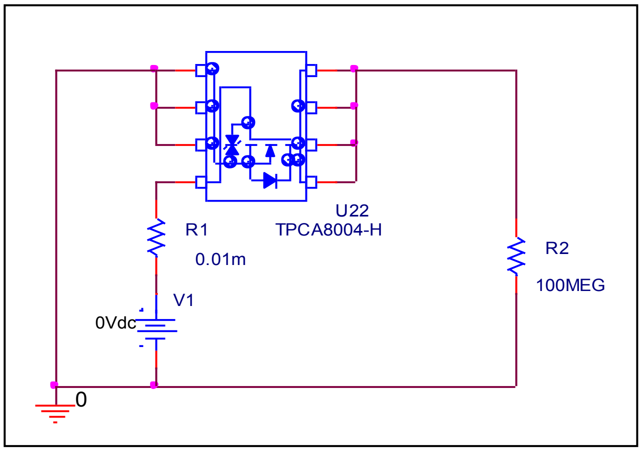
Relation between trj and trb

ESD PROTECTION DIODE
Zener Voltage Characteristic

Circuit Simulation Result

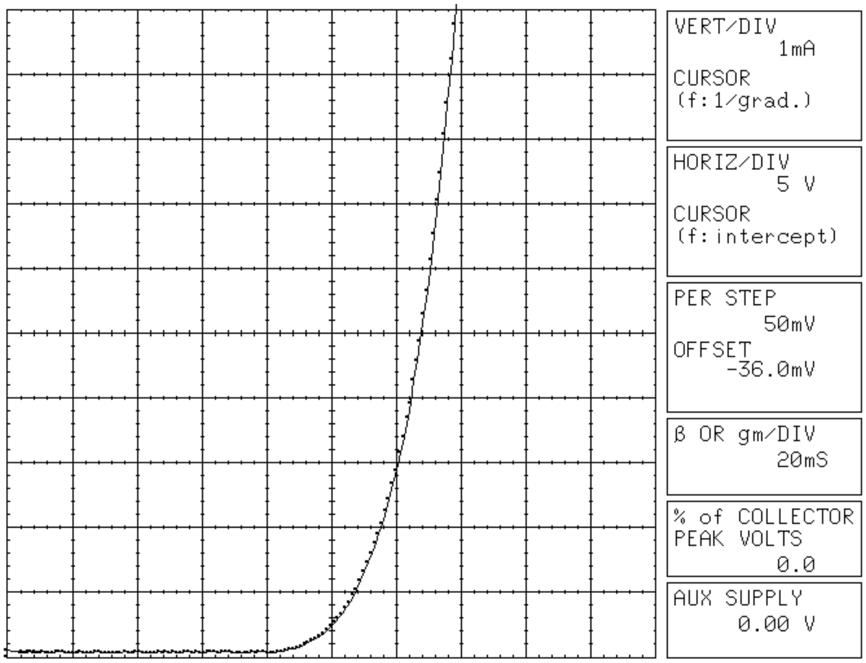


Evaluation Circuit



Zener Voltage Characteristic

Reference



VERT/DIV
1mA
CURSOR
(f:1/grad.)

HORIZ/DIV
5 V
CURSOR
(f:intercept)

PER STEP
50mV
OFFSET
-36.0mV

β OR gm/DIV
20mS

% of COLLECTOR
PEAK VOLTS
0.0

AUX SUPPLY
0.00 V